OIPE
APR 2 9 2004
JC90
PATENT & TRADEMARK OFFICE

TSMC-03-493

April 15, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/772,938 02/05/04

Chii-Ming Wu et al.

METHOD OF FORMING METAL SILICIDE

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 26, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 4/26/04

U.S. Patent 6,468,901 to Maa et al., "Nickel Silicide Including Iridium for Use in Ultra-Shallow Junctions with High Thermal Stability and Method of Manufacturing the Same," discloses an integrated circuit device, and a method of manufacturing the same, including nickel silicide on a silicon substrate fabricated with an iridium interlayer.

U.S. Patent 6,346,477 to Kaloyeros et al., "Method of Interlayer Mediated Epitaxy of Cobalt Silicide from Low Temperature Chemical Vapor Deposition of Cobalt," discusses a process for the preparation of cobalt disilicide films.

U.S. Patent 6,511,867 to Lowrey et al., "Utilizing Atomic Layer Deposition for Programmable Device," discloses an apparatus that sets and reprograms the state of programmable devices.

U.S. Patent 6,423,619 to Grant et al., "Transistor Metal Gate Structure that Minimizes Non-Planarity Effects and Method of Formation," discloses a metal gate structure formed by depositing a gate dielectric, a gate electrode, a stop layer, and a metal layer within a gate trench and removing the portions of the layers that lie outside the gate trench.

Sincerely,

Stephen B. Ackerman, Reg. #37761

Sheet 1 of 1

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

O I P E
JC60
APR 2 9 2004
PATENT & TRADEMARK OFFICE

Docket Number (Optional) TSMC-03-493	Application Number 10/772,938
Applicant Chii-Ming Wu et al.	
Filing Date 02/05/04	Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6468901	10/22/02	Maa et al.	438	655	5/2/01
	6346477	2/12/02	Kaloyeros et al.	438	680	1/9/01
	6511867	1/28/03	Lowrey et al.	438	128	6/30/01
	6423619	7/23/02	Grant et al.	438	589	11/30/01

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.